

Device Modeling Report

COMPONENTS: Power MOSFET (Model Parameter)
PART NUMBER: MP4212
MANUFACTURER: TOSHIBA
Body Diode (Model Parameter) / ESD Protection Diode
REMARK: N&P Channel Model



Bee Technologies Inc.

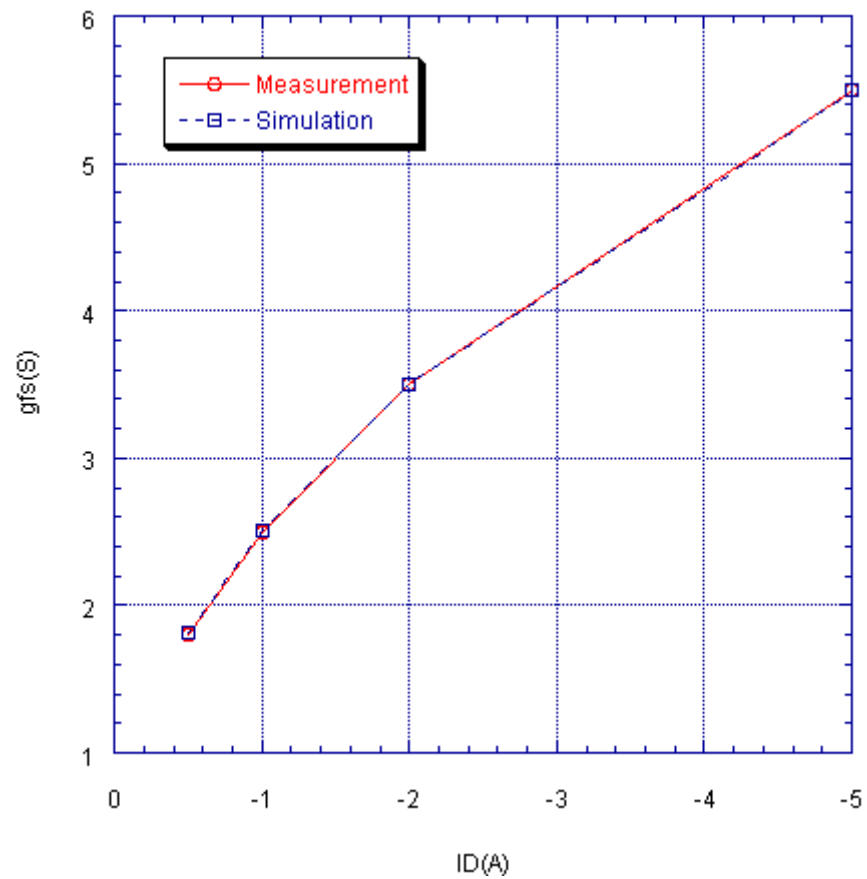
MOSFET MODEL

Pspice model parameter	Model description
LEVEL	
L	Channel Length
W	Channel Width
KP	Transconductance
RS	Source Ohmic Resistance
RD	Ohmic Drain Resistance
VTO	Zero-bias Threshold Voltage
RDS	Drain-Source Shunt Resistance
TOX	Gate Oxide Thickness
CGSO	Zero-bias Gate-Source Capacitance
CGDO	Zero-bias Gate-Drain Capacitance
CBD	Zero-bias Bulk-Drain Junction Capacitance
MJ	Bulk Junction Grading Coefficient
PB	Bulk Junction Potential
FC	Bulk Junction Forward-bias Capacitance Coefficient
RG	Gate Ohmic Resistance
IS	Bulk Junction Saturation Current
N	Bulk Junction Emission Coefficient
RB	Bulk Series Resistance
PHI	Surface Inversion Potential
GAMMA	Body-effect Parameter
DELTA	Width effect on Threshold Voltage
ETA	Static Feedback on Threshold Voltage
THETA	Modility Modulation
KAPPA	Saturation Field Factor
VMAX	Maximum Drift Velocity of Carriers
XJ	Metallurgical Junction Depth
UO	Surface Mobility

P-Channel Model

Transconductance Characteristic

Circuit Simulation Result

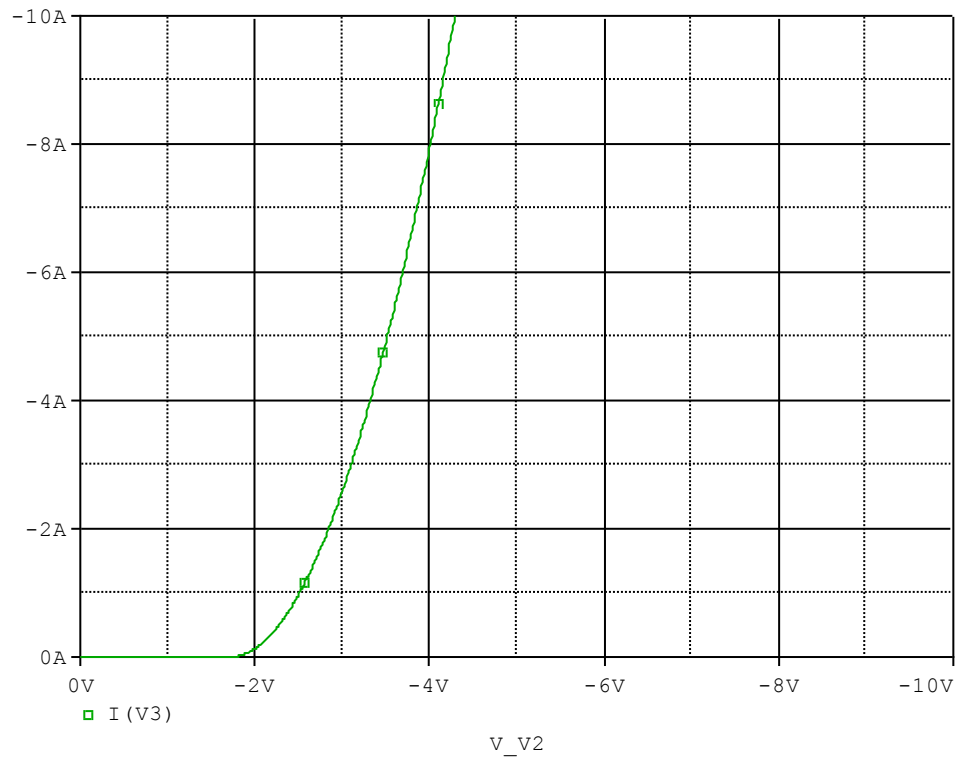


Comparison table

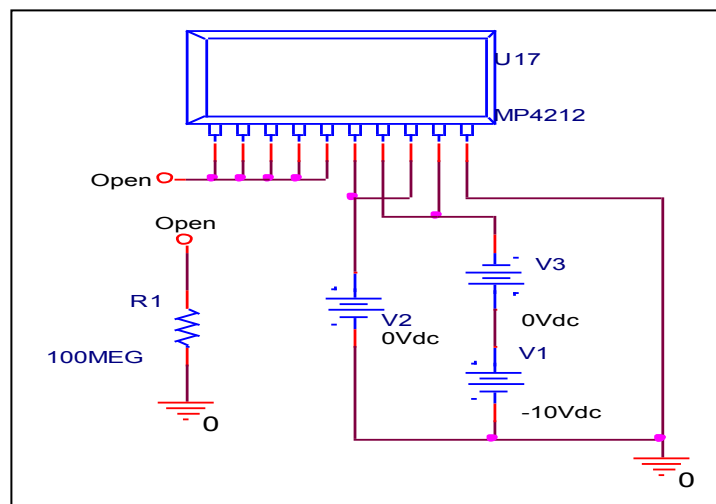
Id(A)	gfs		Error(%)
	Measurement	Simulation	
-0.500	1.800	1.810	0.556
-1.000	2.500	2.505	0.200
-2.000	3.500	3.500	0.000
-5.000	5.500	5.505	0.091

V_{gs}-I_d Characteristic

Circuit Simulation result

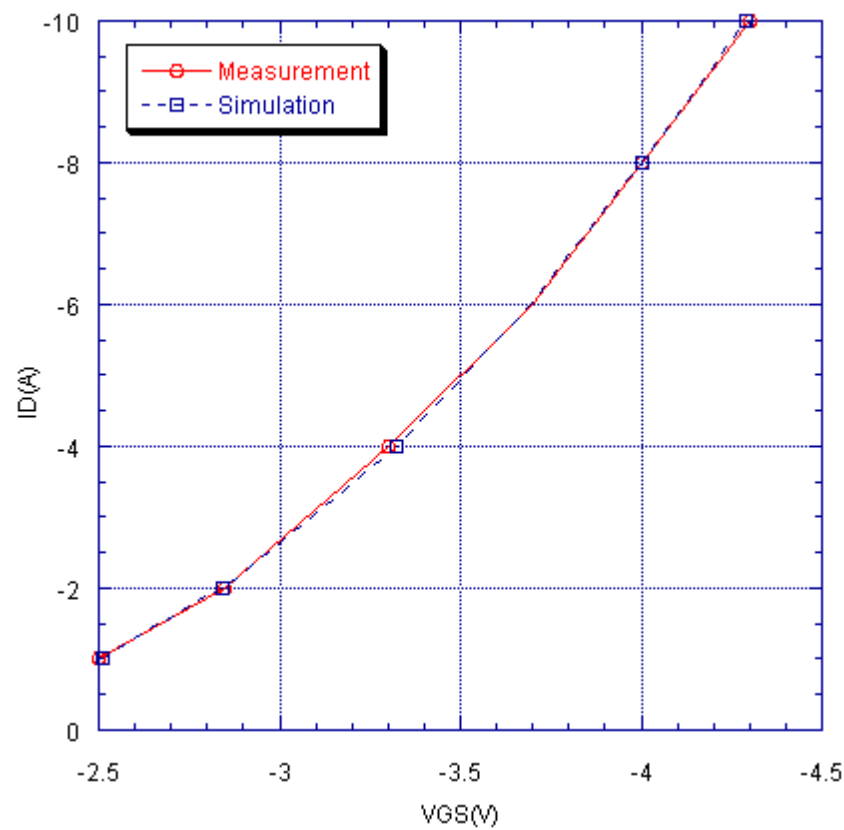


Evaluation circuit



Comparison Graph

Circuit Simulation Result

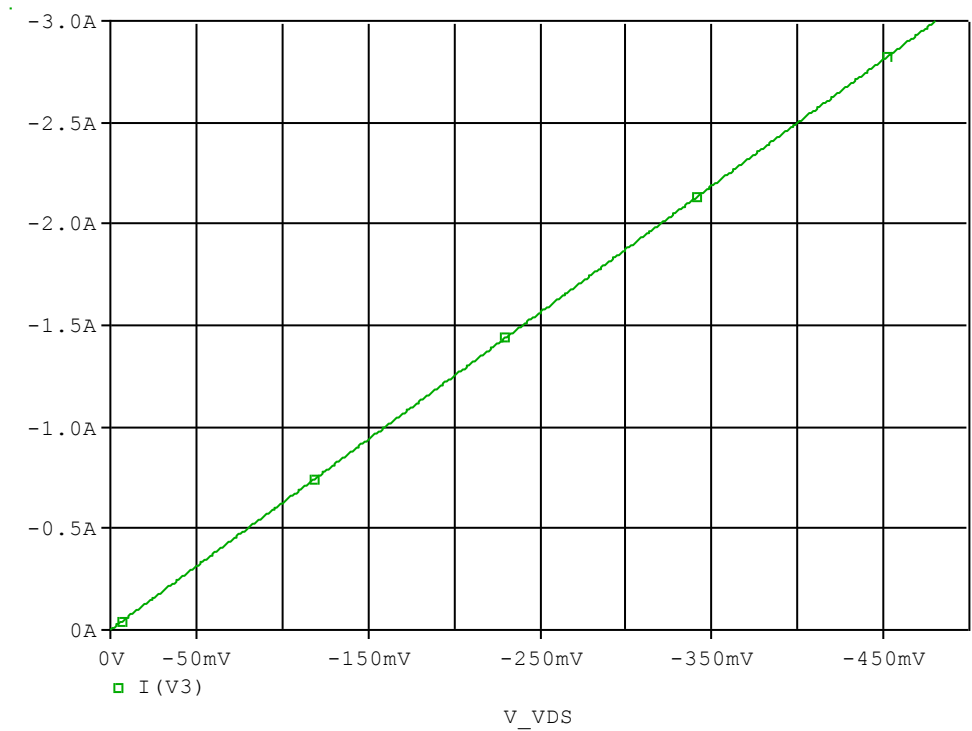


Simulation Result

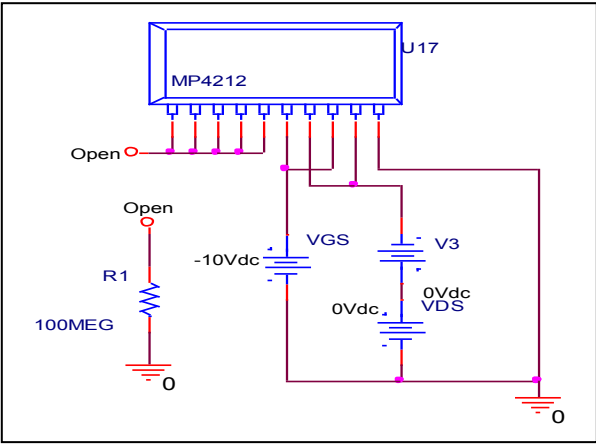
I_D (A)	V_{GS} (V)		Error (%)
	Measurement	Simulation	
-1.000	-2.500	-2.511	0.440
-2.000	-2.850	-2.844	-0.211
-4.000	-3.300	-3.324	0.727
-6.000	-3.700	-3.695	-0.135
-8.000	-4.000	-4.004	0.100
-10.000	-4.300	-4.291	-0.209

Rds(on) Characteristic

Circuit Simulation result



Evaluation circuit

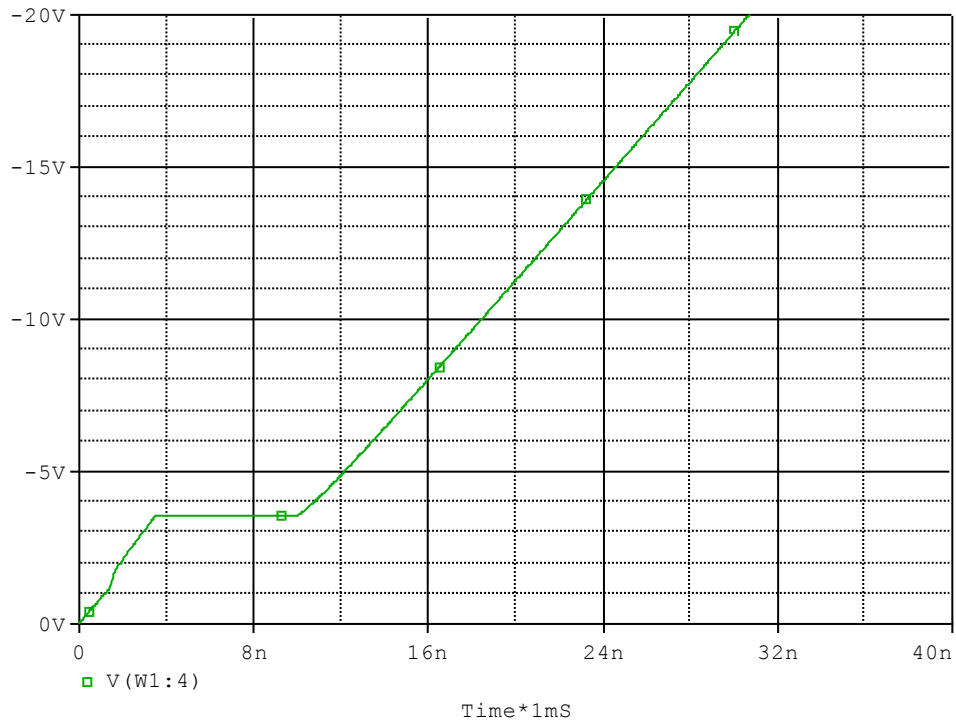


Simulation Result

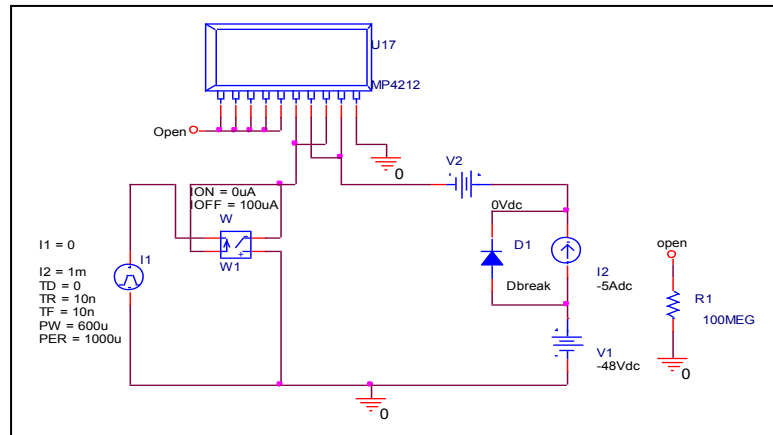
$I_D = -2.5A, V_{GS} = -10V$	Measurement		Simulation		Error (%)
$R_{DS(on)}$	400.000	mΩ	400.000	mΩ	0.000

Gate Charge Characteristic

Circuit Simulation result



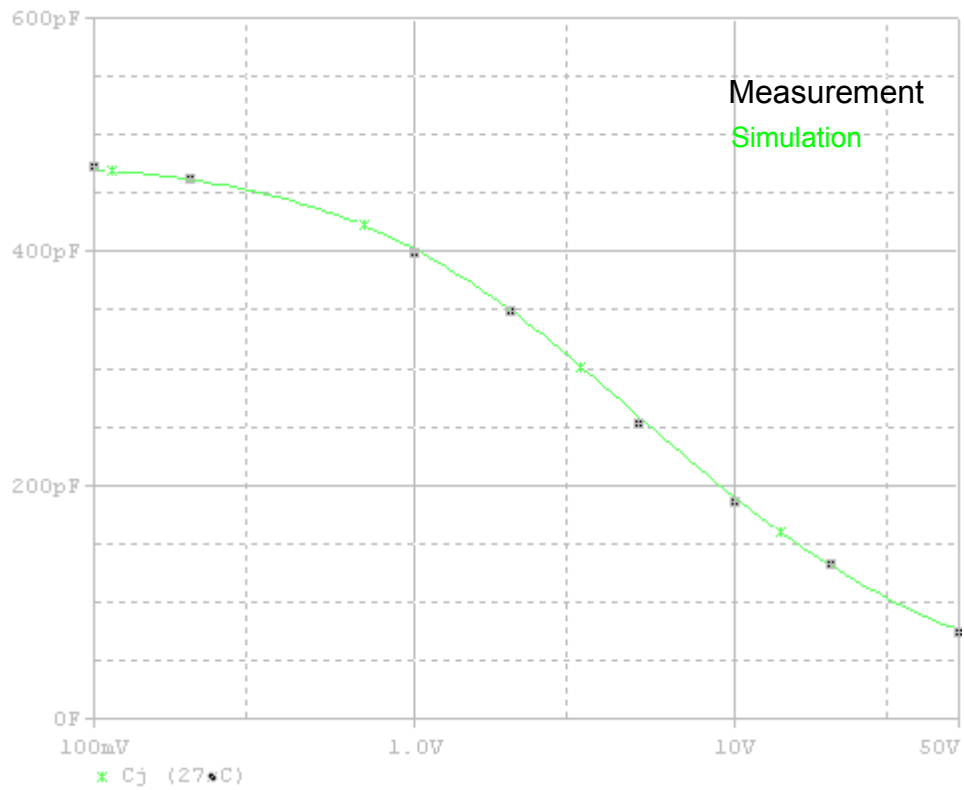
Evaluation circuit



Simulation Result

$V_{DD}=-48V, I_D=-5A$ $V_{GS}=-10V$	Measurement		Simulation		Error (%)
Qgs	3.500	nC	3.545	nC	1.286
Qgd	10.000	nC	10.046	nC	0.460
Qg	22.000	nC	18.364	nC	-16.527

Capacitance Characteristic

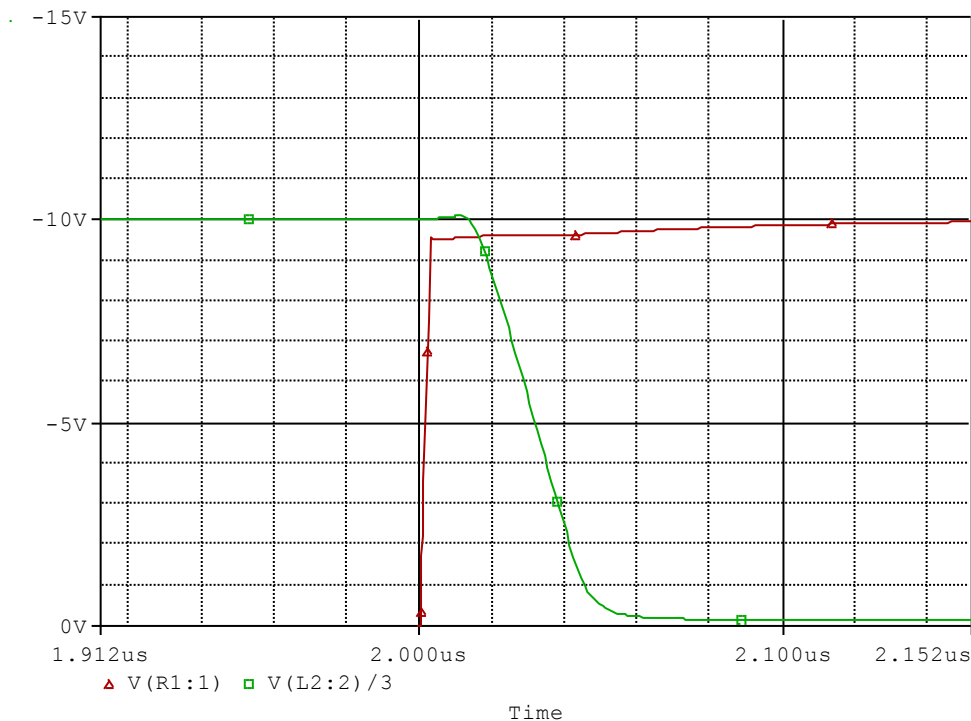


Simulation Result

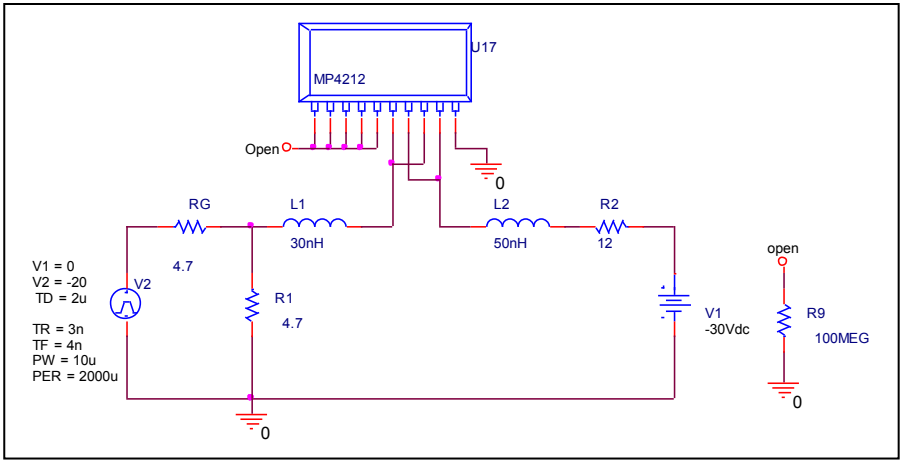
V_{DS} (V)	Cbd(pF)		Error(%)
	Measurement	Simulation	
0.100	475.000	471.000	-0.842
0.200	465.000	462.000	-0.645
0.500	440.000	438.000	-0.455
1.000	400.000	403.000	0.750
2.000	350.000	351.000	0.286
5.000	255.000	260.000	1.961
10.000	188.000	190.000	1.064
20.000	134.000	135.000	0.746
50.000	75.000	75.000	0.000

Switching Time Characteristic

Circuit Simulation result



Evaluation circuit

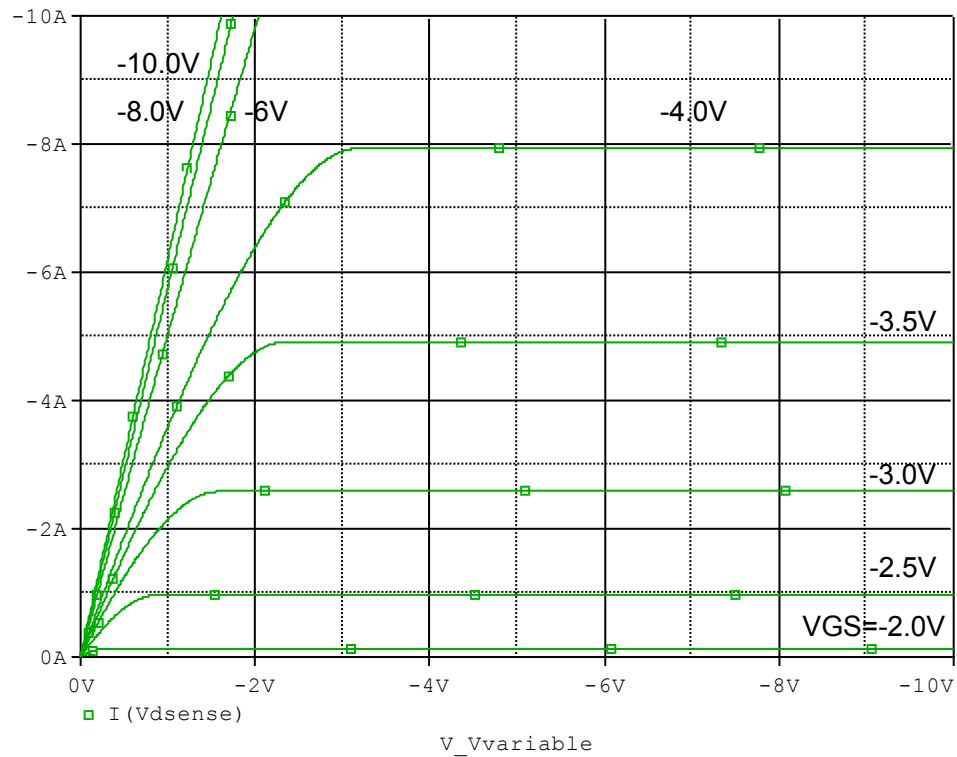


Simulation Result

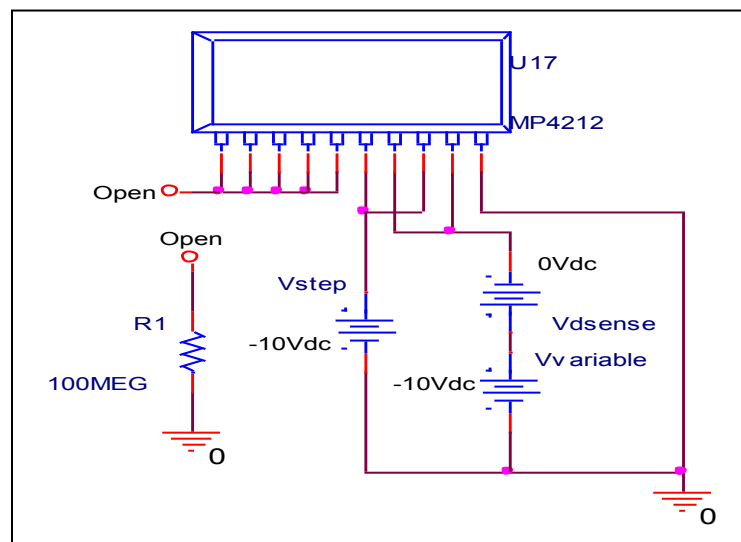
$I_D = -2.5A$, $V_{DD} = -30V$ $V_{GS} = 0/10V$	Measurement		Simulation		Error(%)
	ton	ns	44.933	ns	
					-0.149

Output Characteristic

Circuit Simulation result



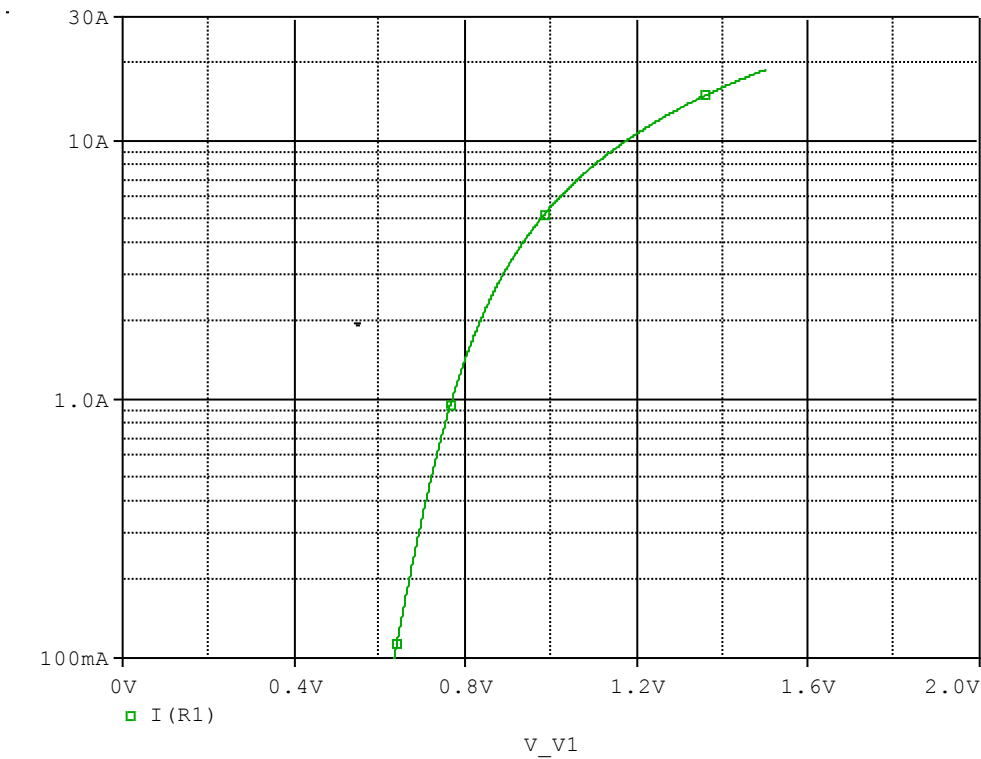
Evaluation circuit



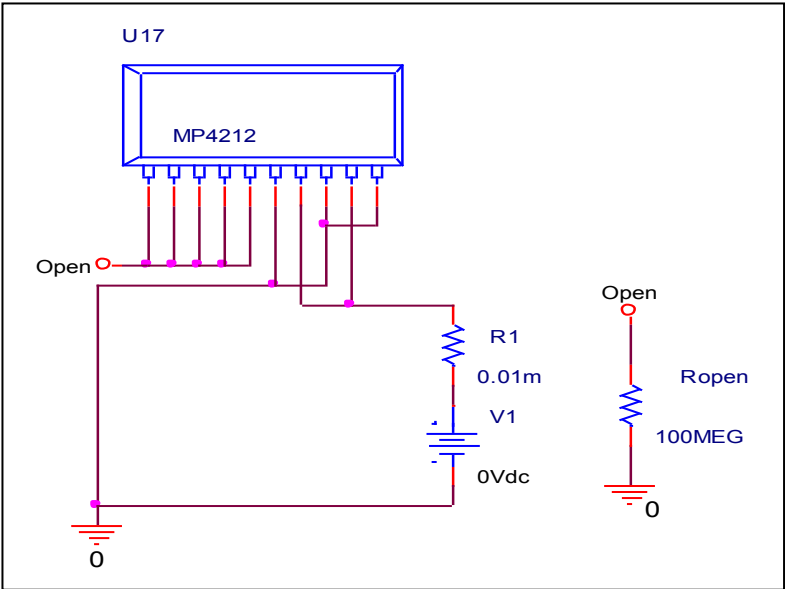
BODY DIODE

Forward Current Characteristic

Circuit Simulation Result

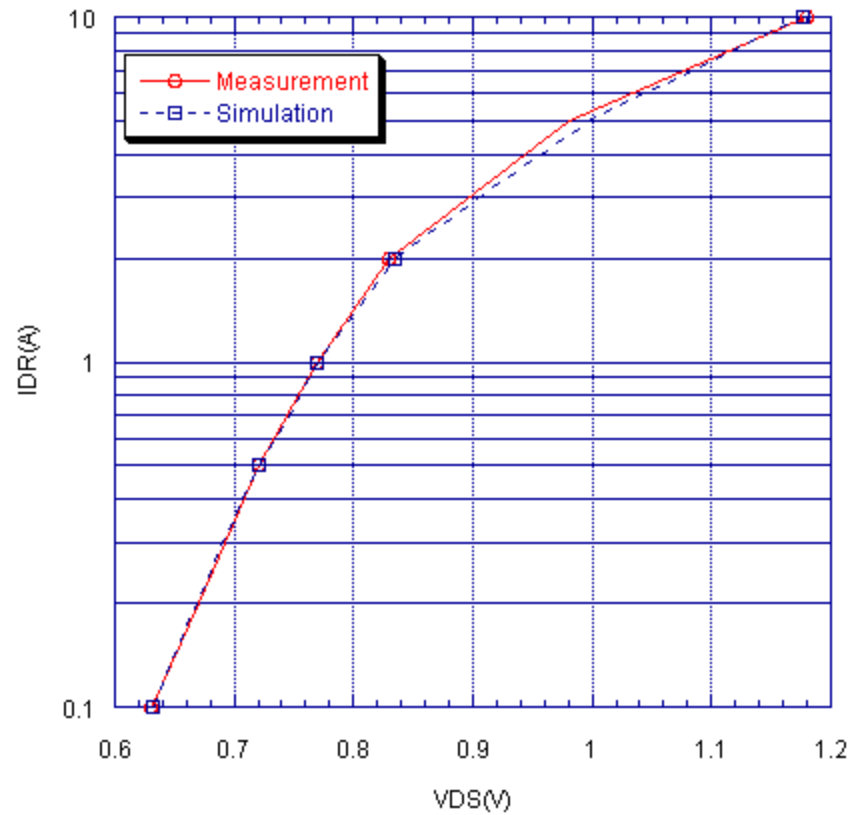


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

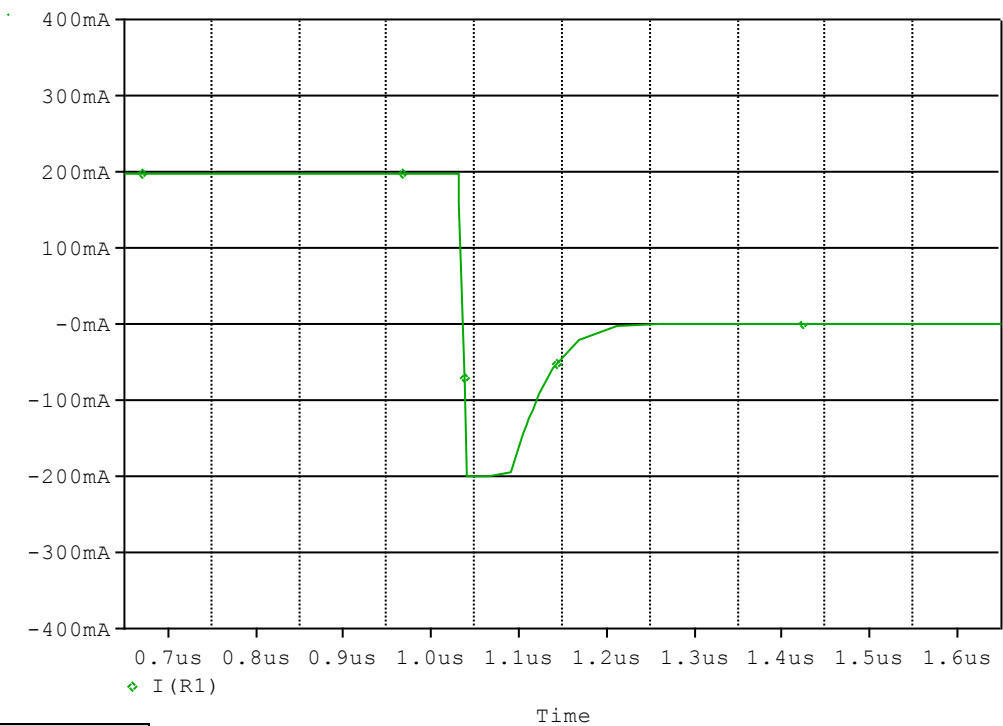


Simulation Result

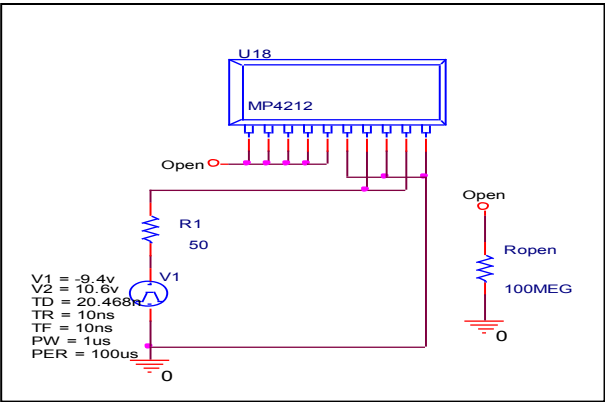
IDR(A)	VDS(V) Measurement	VDS(V) Simulation	%Error
0.100	0.630	0.632	0.317
0.200	0.670	0.668	-0.299
0.500	0.720	0.720	0.000
1.000	0.770	0.769	-0.130
2.000	0.830	0.834	0.482
5.000	0.980	0.997	1.735
10.000	1.180	1.177	-0.254

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

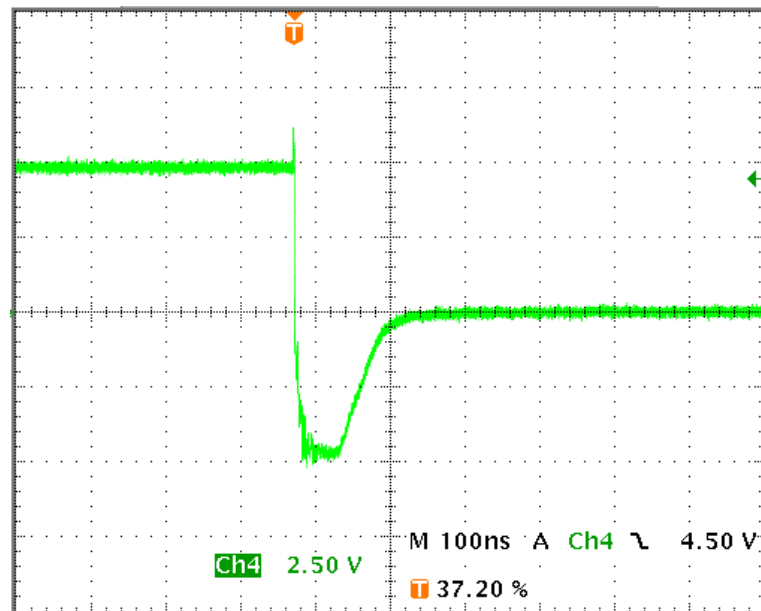


Compare Measurement vs. Simulation

	Measurement		Simulation		Error (%)
trj	50.000	ns	49.878	ns	-0.244
trb	76.000	ns	82.207	ns	8.167
trr	126.000	ns	132.085	ns	4.829

Reverse Recovery Characteristic

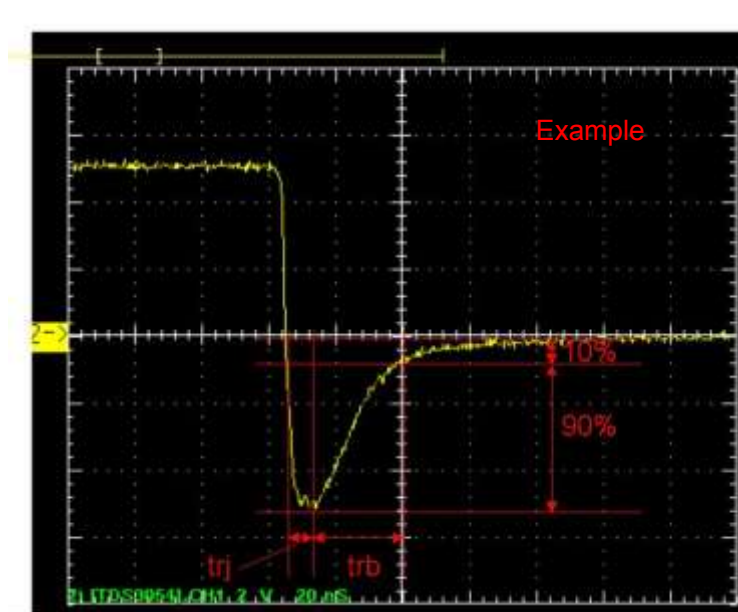
Reference



$T_{rr}=50(\text{ns})$

$T_{rb}=76(\text{ns})$

Conditions: $I_{fwd}=I_{rev}=0.2(\text{A})$, $R_I=50$

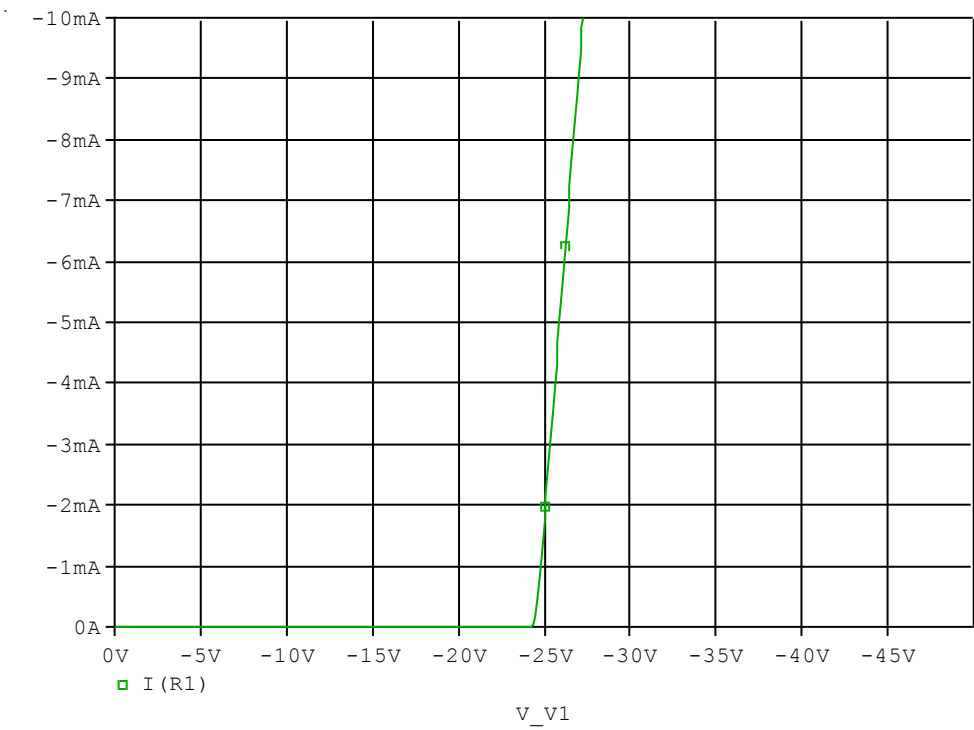


Relation between t_{rr} and t_{rb}

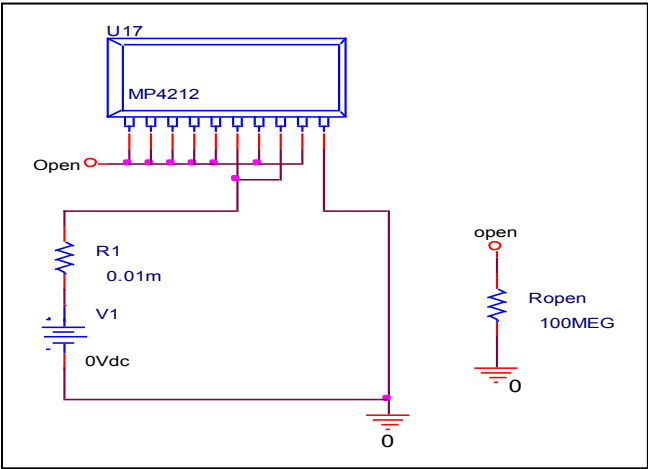
ESD PROTECTION DIODE

Zener Voltage Characteristic

Circuit Simulation Result

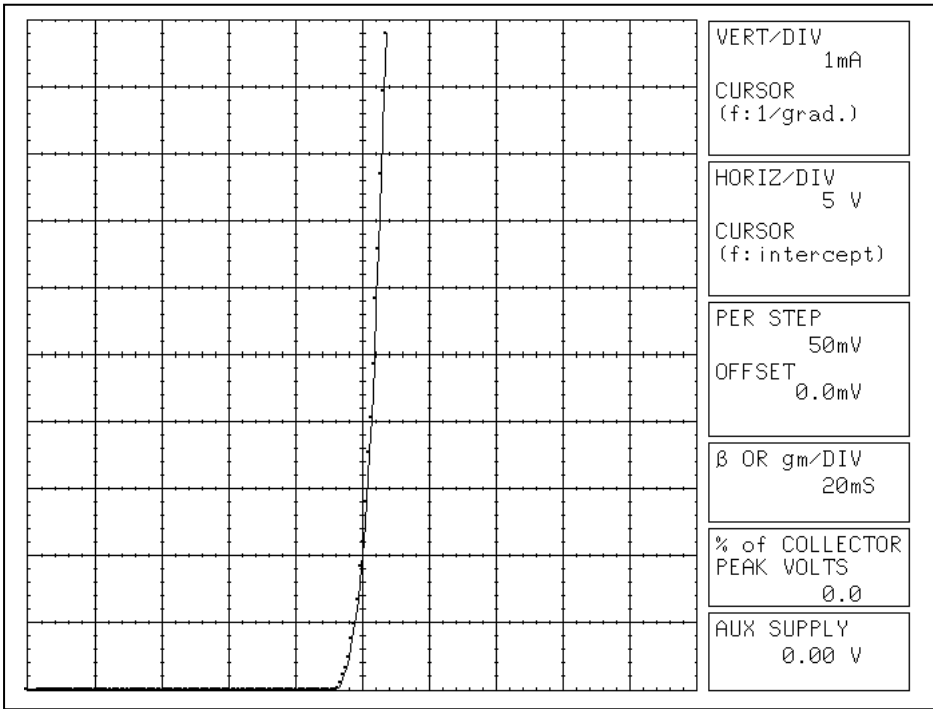


Evaluation Circuit



Zener Voltage Characteristic

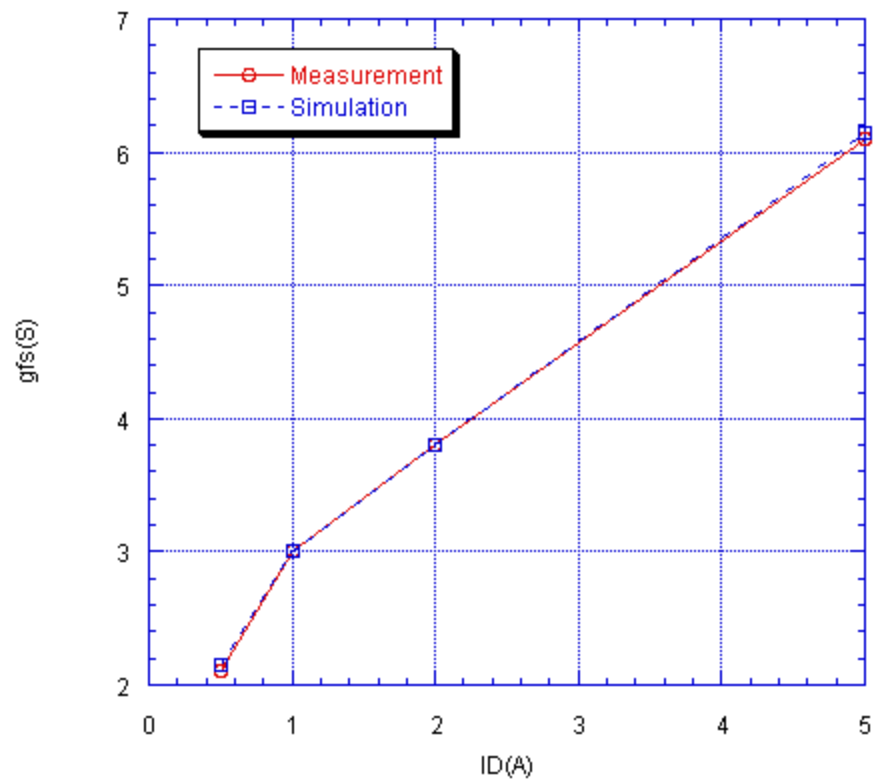
Reference



N-Channel Model

Transconductance Characteristic

Circuit Simulation Result

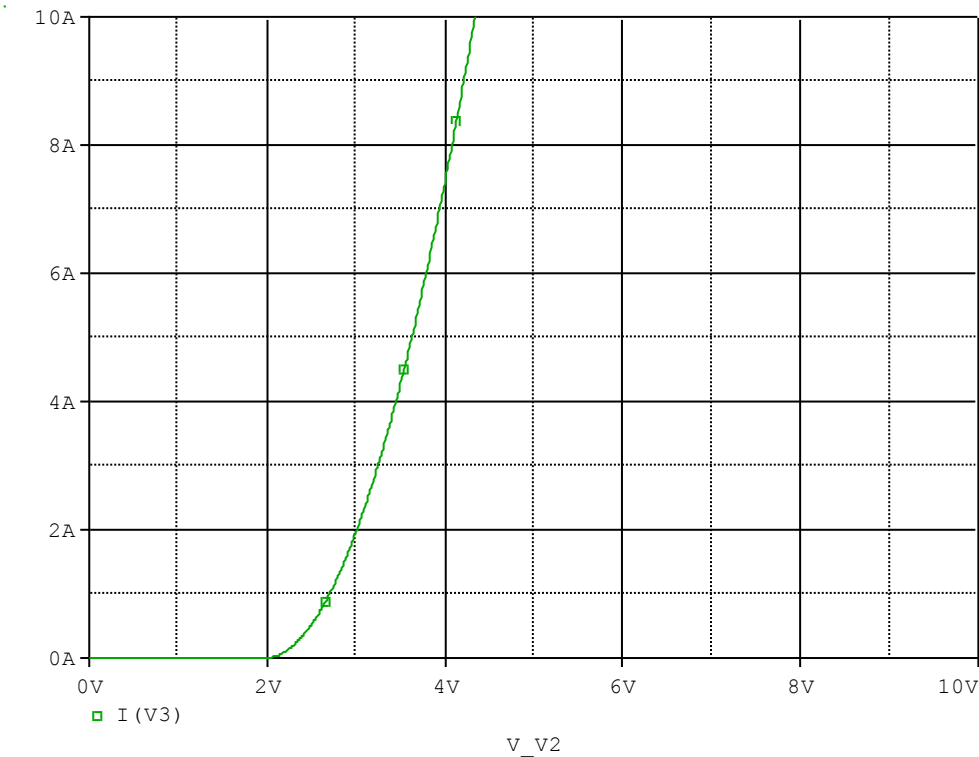


Comparison table

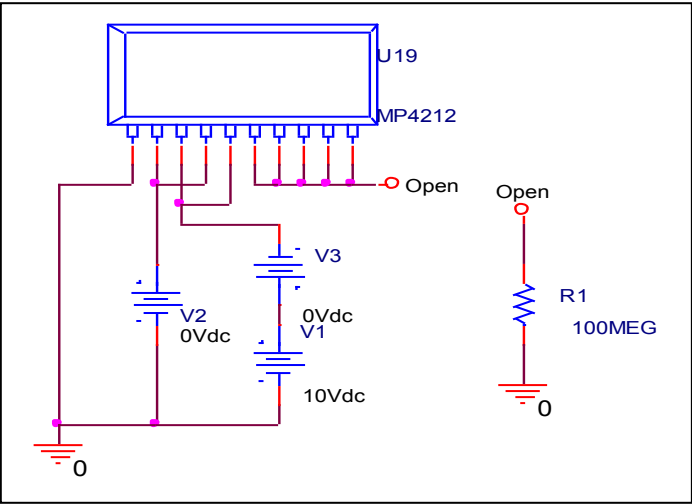
Id(A)	gfs		Error(%)
	Measurement	Simulation	
0.500	2.100	2.150	2.381
1.000	3.000	3.010	0.333
2.000	3.800	3.800	0.000
5.000	6.100	6.150	0.820

Vgs-Id Characteristic

Circuit Simulation result

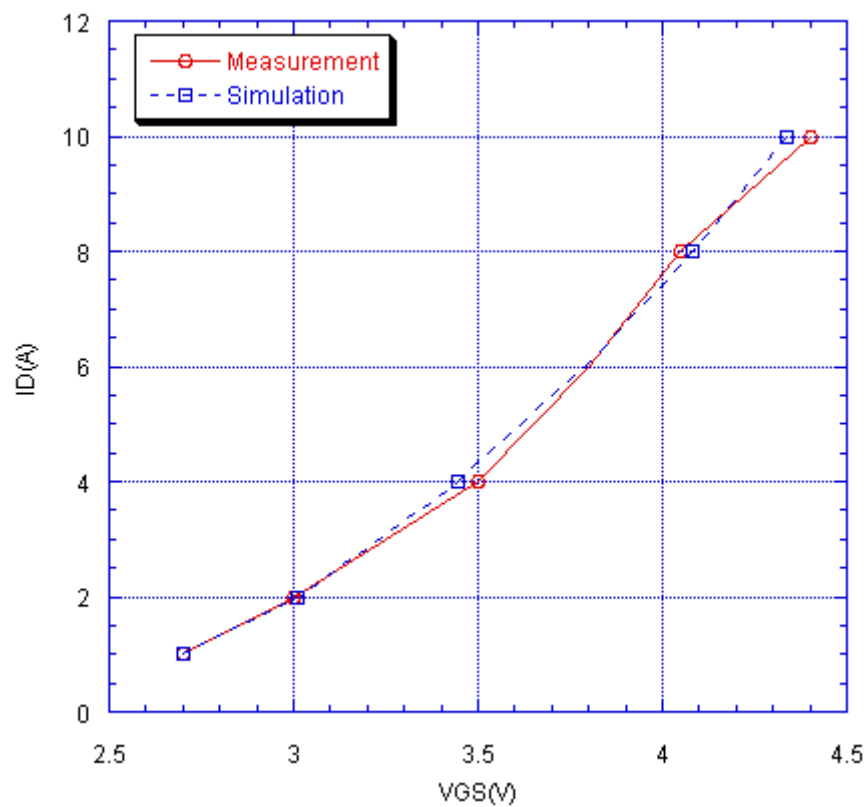


Evaluation circuit



Comparison Graph

Circuit Simulation Result

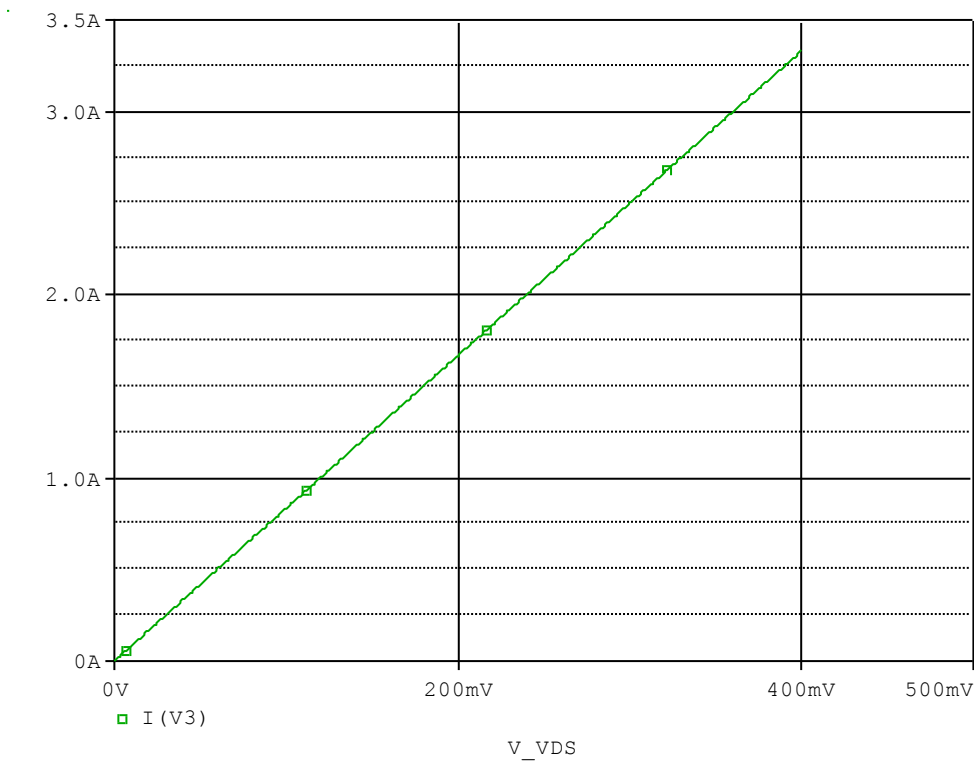


Simulation Result

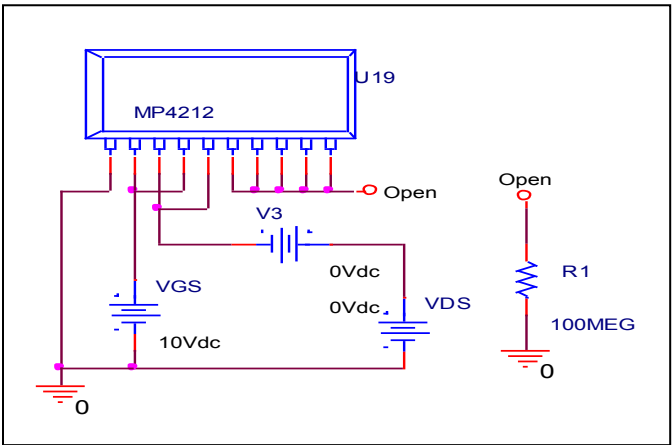
I_D (A)	V_{GS} (V)		Error (%)
	Measurement	Simulation	
1.000	2.700	2.701	0.037
2.000	3.000	3.011	0.367
4.000	3.500	3.446	-1.543
6.000	3.800	3.790	-0.263
8.000	4.000	4.081	2.025
10.000	4.400	4.339	-1.386

Rds(on) Characteristic

Circuit Simulation result



Evaluation circuit

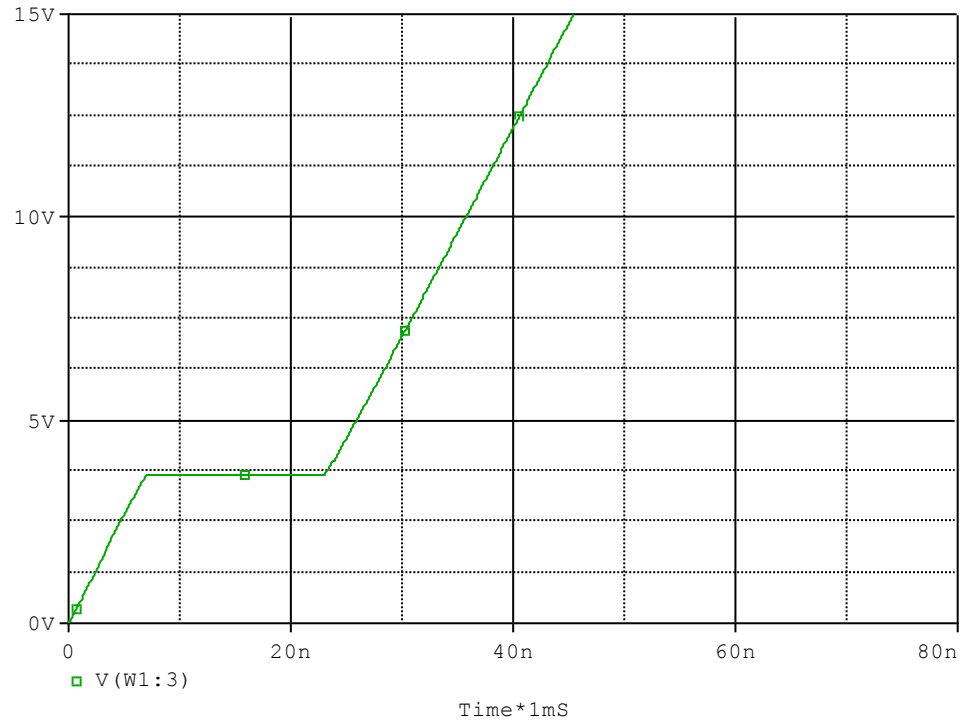


Simulation Result

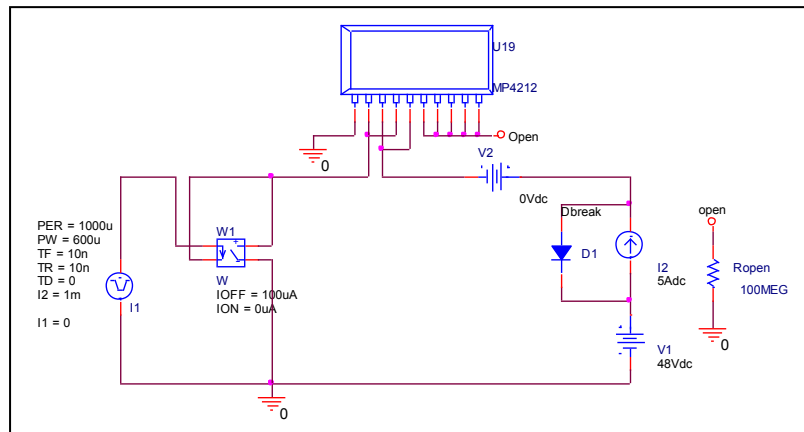
$I_D=2.5A, V_{GS}=10V$	Measurement		Simulation		Error (%)
$R_{DS(on)}$	300.000	mΩ	300.000	mΩ	0.000

Gate Charge Characteristic

Circuit Simulation result



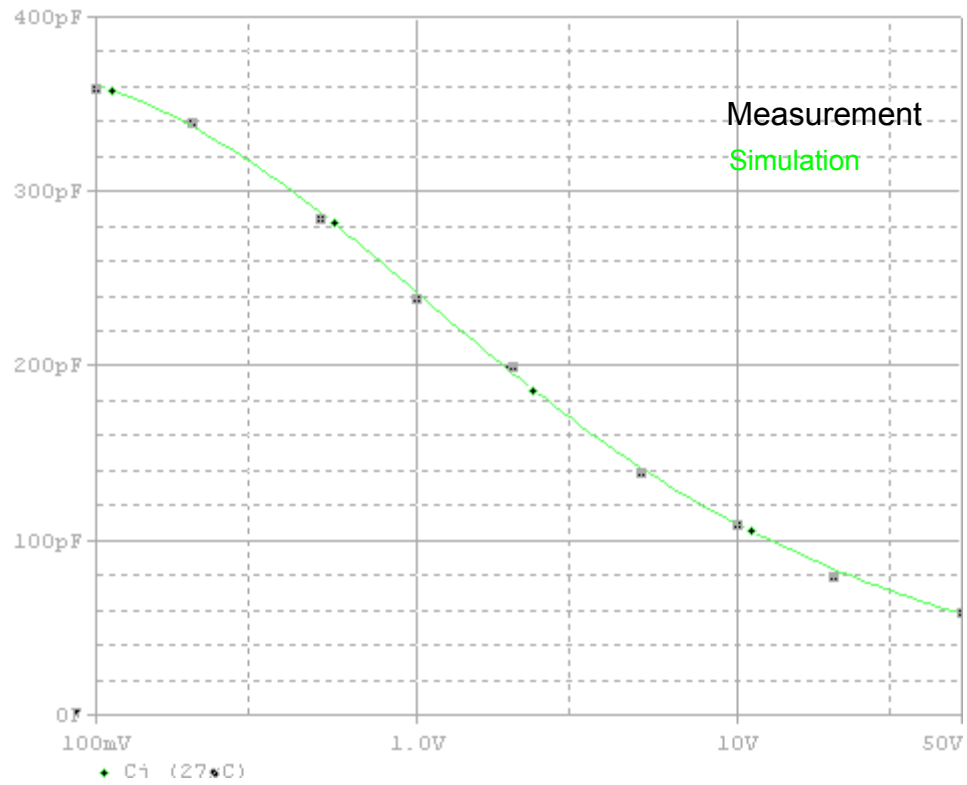
Evaluation circuit



Simulation Result

$V_{DD}=48V, I_D=5A$ $V_{GS}=10V$	Measurement		Simulation		Error (%)
Qgs	7.000	nC	7.009	nC	0.129
Qgd	16.000	nC	15.963	nC	-0.231
Qg	45.000	nC	35.734	nC	-20.591

Capacitance Characteristic

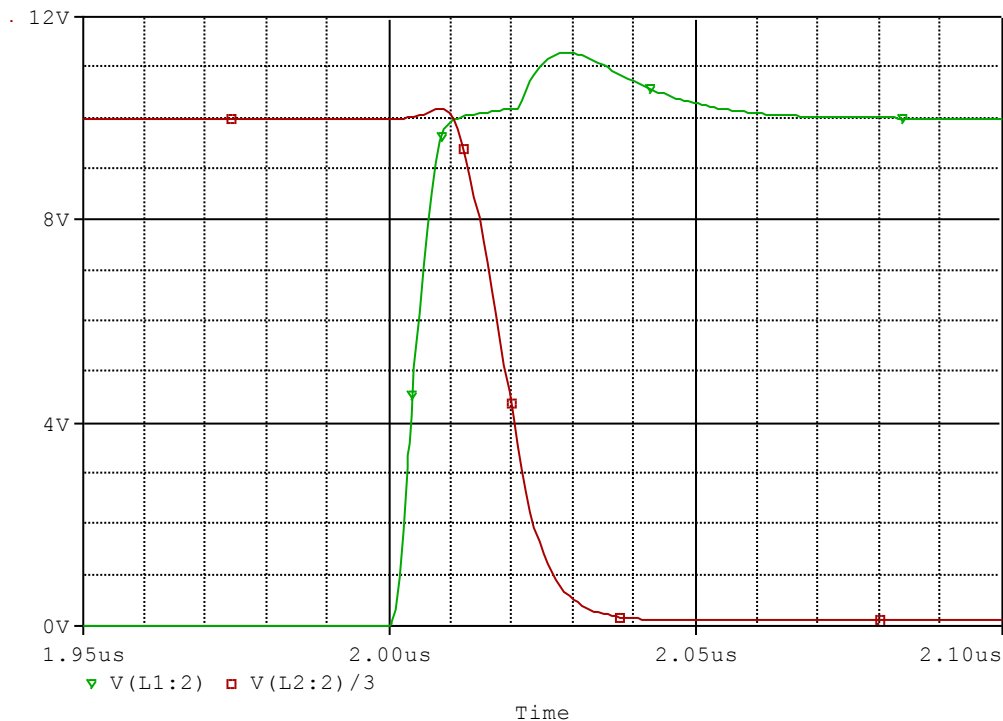


Simulation Result

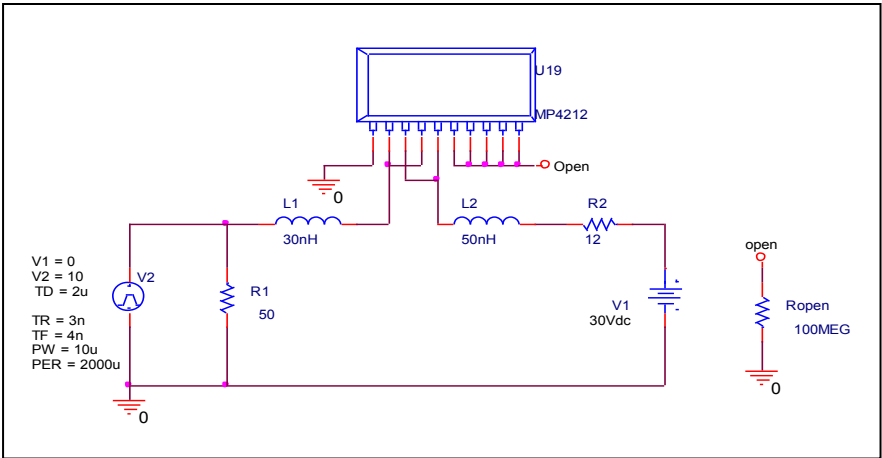
V_{DS} (V)	Cbd(pF)		Error(%)
	Measurement	Simulation	
0.100	360.000	362.000	0.556
0.200	340.000	337.000	-0.882
0.500	285.000	288.000	1.053
1.000	240.000	243.000	1.250
2.000	200.000	198.000	-1.000
5.000	140.000	142.000	1.429
10.000	110.000	110.000	0.000
20.000	80.000	83.000	3.750
50.000	60.000	61.000	1.667

Switching Time Characteristic

Circuit Simulation result



Evaluation circuit

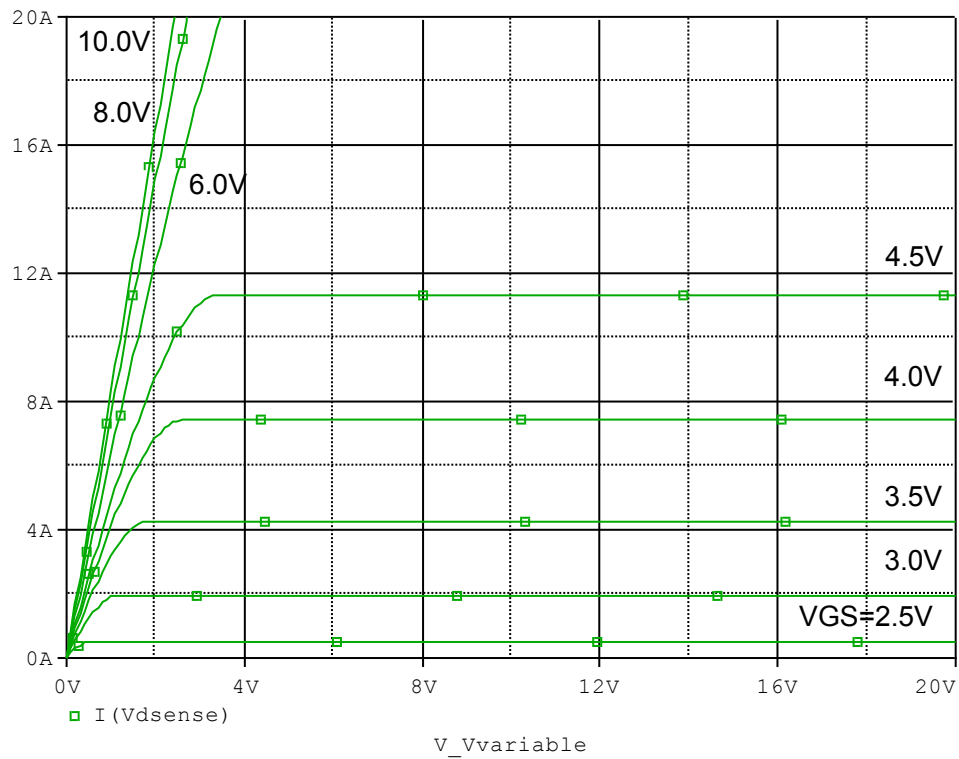


Simulation Result

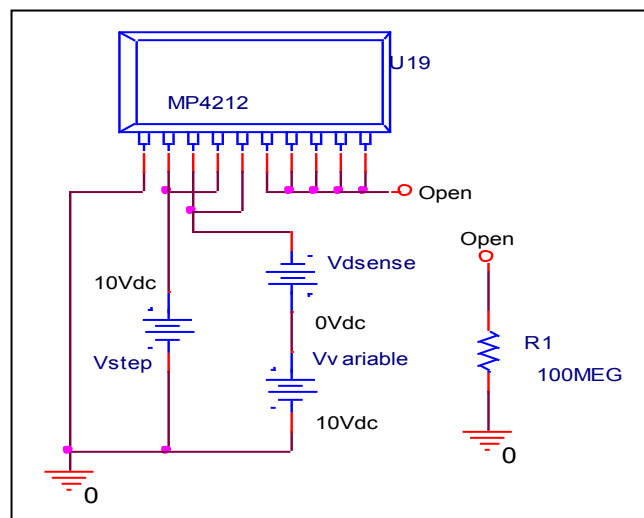
$I_D=2.5\text{ A}$, $V_{DD}=30\text{ V}$ $V_{GS}=0/10\text{ V}$	Measurement		Simulation		Error(%)
	ton	25.000 ns	25.042 ns	ns	
					-0.168

Output Characteristic

Circuit Simulation result

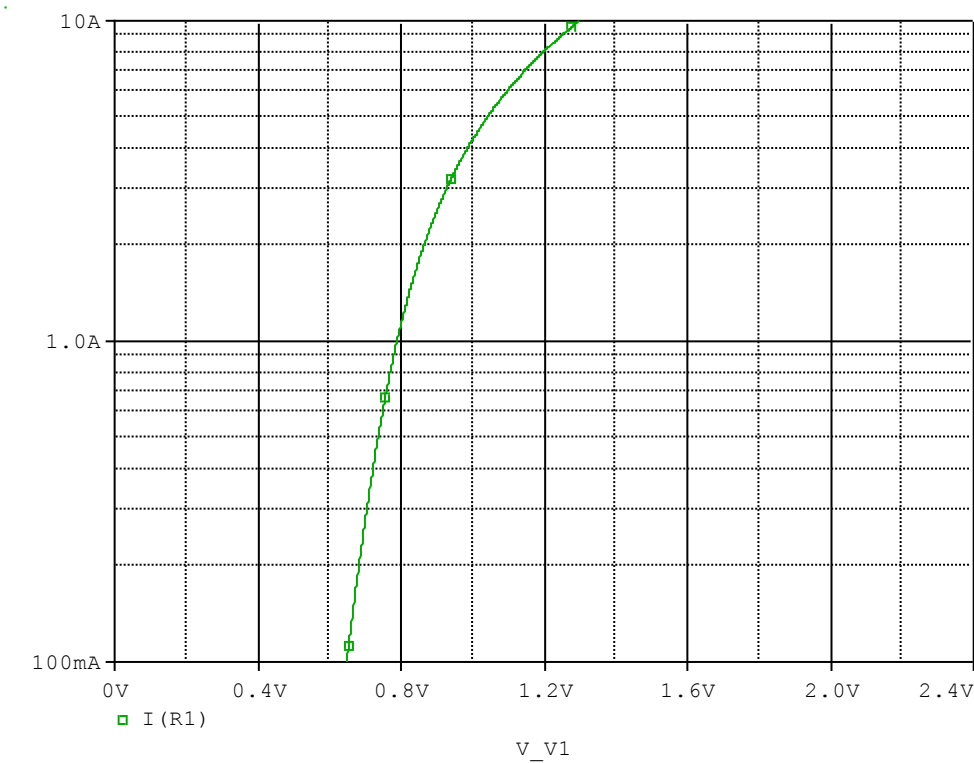


Evaluation circuit

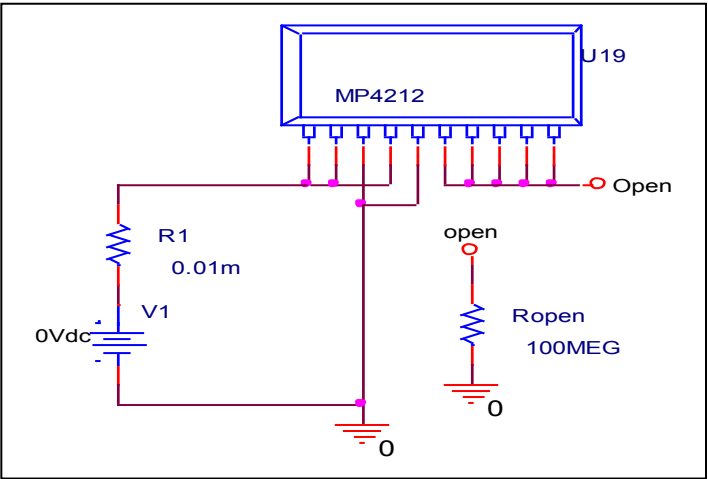


BODY DIODE Forward Current Characteristic

Circuit Simulation Result

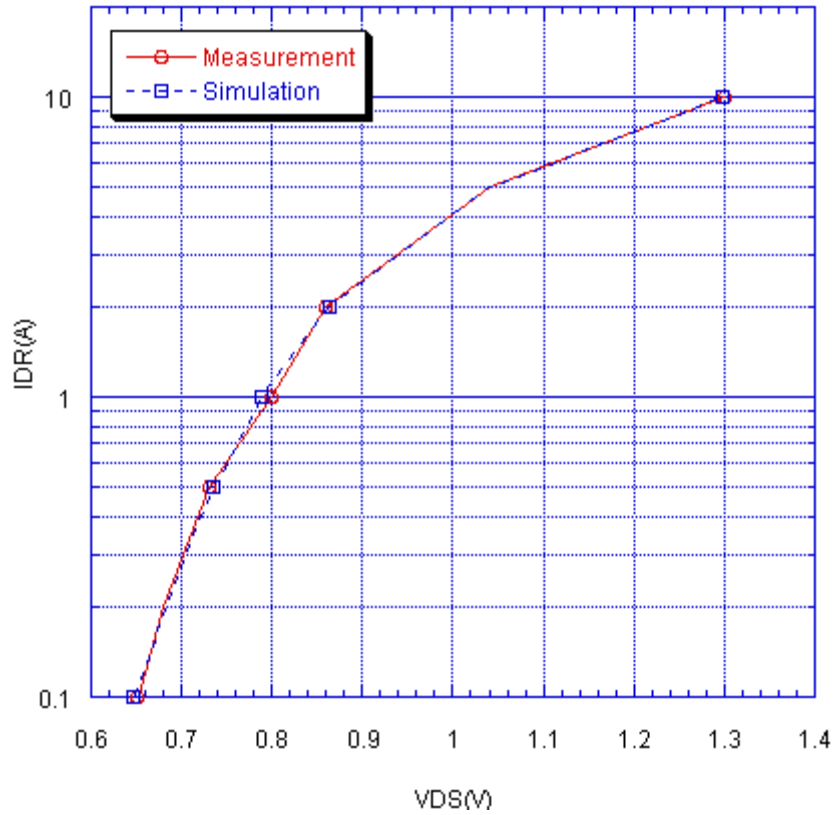


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

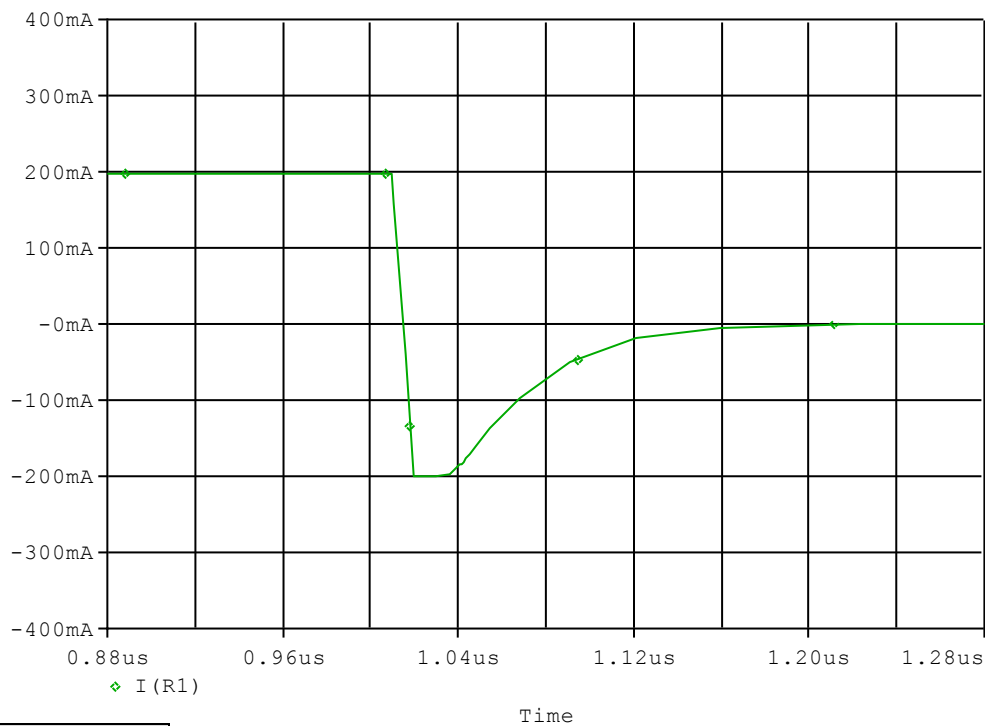


Simulation Result

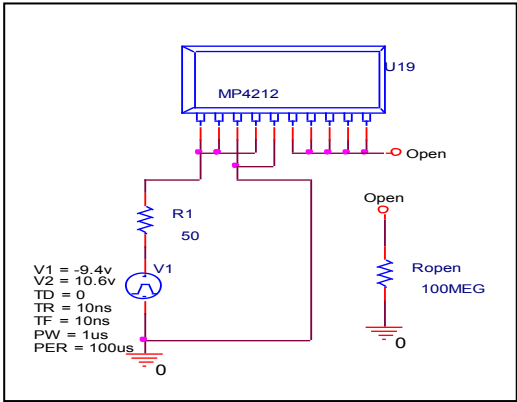
IDR(A)	VSD(V)	VSD(V)	%Error
	Measurement	Simulation	
0.100	0.650	0.647	-0.462
0.200	0.680	0.682	0.294
0.500	0.730	0.736	0.822
1.000	0.800	0.789	-1.375
2.000	0.860	0.864	0.465
5.000	1.040	1.041	0.096
10.000	1.300	1.299	-0.077

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

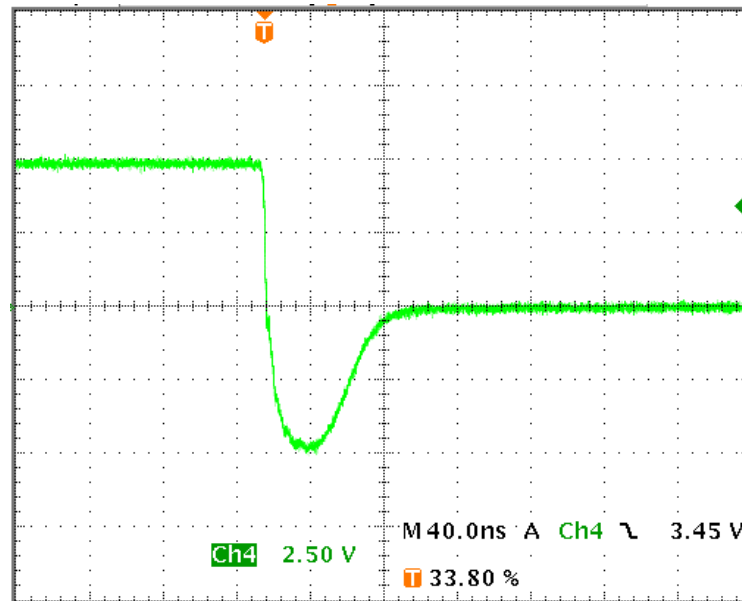


Compare Measurement vs. Simulation

	Measurement		Simulation		Error (%)
trj	22.400	ns	22.266	ns	-0.598
trb	40.000	ns	82.273	ns	105.682
trr	62.000	ns	104.539	ns	67.530

Reverse Recovery Characteristic

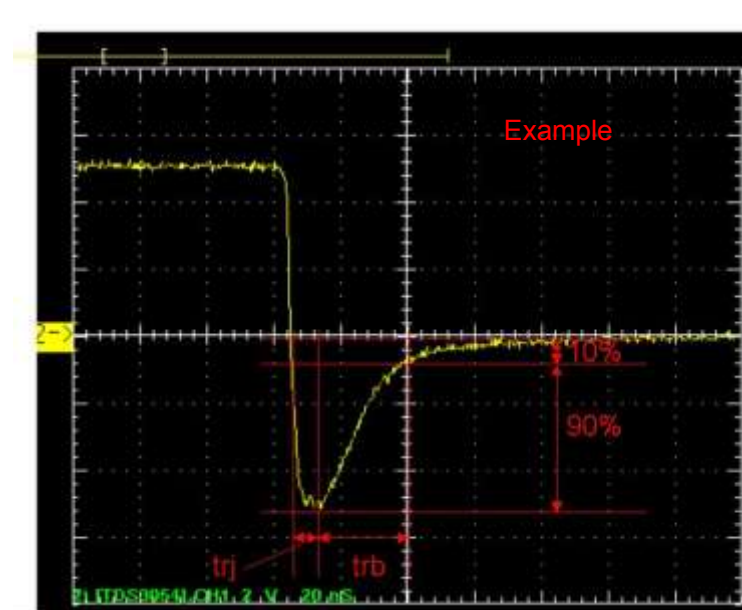
Reference



$Trj=22.4(ns)$

$Trb=40.0(ns)$

Conditions: $I_{fwd}=I_{rev}=0.2(A)$, $R_I=50$

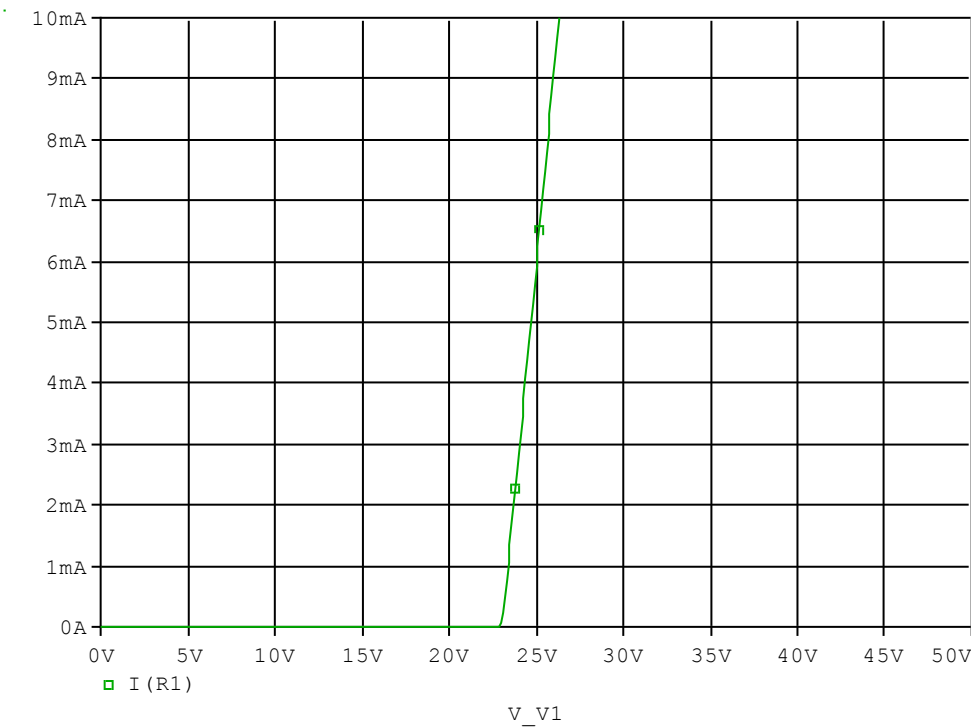


Relation between trj and trb

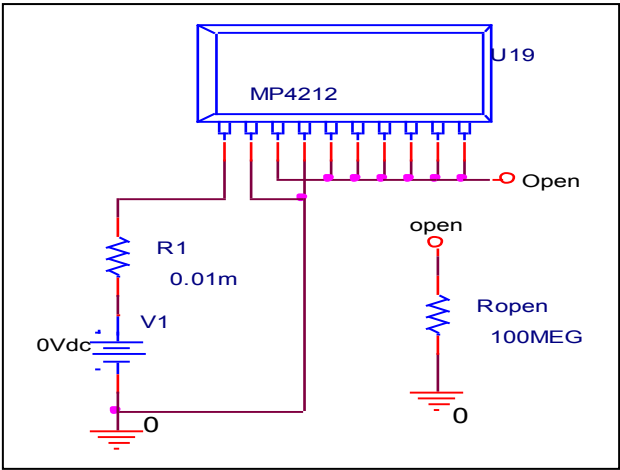
ESD PROTECTION DIODE

Zener Voltage Characteristic

Circuit Simulation Result



Evaluation Circuit



Zener Voltage Characteristic

Reference

